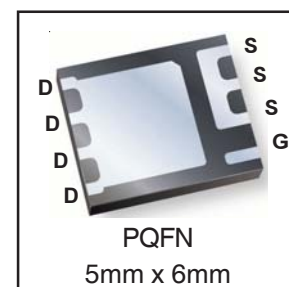
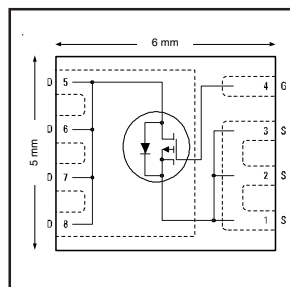


IRFH9310PbF

HEXFET® Power MOSFET

V_{DS}	-30	V
$R_{DS(on) \text{ max}}$ (@ $V_{GS} = 10V$)	4.6	mΩ
Q_g (typical)	110	nC
R_G (typical)	2.8	Ω
I_D (@ $T_A = 25^\circ\text{C}$)	-21	A



Applications

- Charge and Discharge Switch for Notebook PC Battery Application

Features and Benefits

Features

Low $R_{DS(on)}$ ($\leq 4.6\text{m}\Omega$)
Industry-Standard PQFN Package
RoHS Compliant Containing no Lead, no Bromide and no Halogen

results in
⇒

Resulting Benefits

Lower Conduction Losses
Multi-Vendor Compatibility
Environmentally Friendlier

Orderable part number	Package Type	Standard Pack		Note
		Form	Quantity	
IRFH9310TRPBF	PQFN 5mm x 6mm	Tape and Reel	4000	

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	-30	V
V_{GS}	Gate-to-Source Voltage	± 20	
I_D @ $T_A = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ -10V	-21	A
I_D @ $T_A = 70^\circ\text{C}$	Continuous Drain Current, V_{GS} @ -10V	-17	
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ -10V (Silicon Limited)	-107	
I_D @ $T_C = 70^\circ\text{C}$	Continuous Drain Current, V_{GS} @ -10V (Silicon Limited)	-86	
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ -10V (Package Limited)	-40	
I_{DM}	Pulsed Drain Current ①	-170	
P_D @ $T_A = 25^\circ\text{C}$	Power Dissipation ④	3.1	W
P_D @ $T_A = 70^\circ\text{C}$	Power Dissipation ④	2.0	
	Linear Derating Factor	0.025	W/°C
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C

Notes ① through ⑥ are on page 2

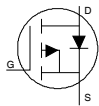
Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	-30	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.020	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = -1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	3.7	4.6	$m\Omega$	$V_{GS} = -10V, I_D = -21A$ ③
		—	5.7	7.1		$V_{GS} = -4.5V, I_D = -17A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	-1.3	-1.9	-2.4	V	$V_{DS} = V_{GS}, I_D = -100\mu A$
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-5.8	—	mV/ $^\circ\text{C}$	
I_{DSS}	Drain-to-Source Leakage Current	—	—	-1.0	μA	$V_{DS} = -24V, V_{GS} = 0V$
		—	—	-150		$V_{DS} = -24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 20V$
g_{fs}	Forward Transconductance	39	—	—	S	$V_{DS} = -10V, I_D = -17A$
Q_g	Total Gate Charge ⑥	—	58	—	nC	$V_{DS} = -15V, V_{GS} = -4.5V, I_D = -17A$
Q_g	Total Gate Charge ⑥	—	110	165	nC	$V_{GS} = -10V$
Q_{gs}	Gate-to-Source Charge ⑥	—	17	—		$V_{DS} = -15V$
Q_{gd}	Gate-to-Drain Charge ⑥	—	28	—		$I_D = -17A$
R_G	Gate Resistance ⑥	—	2.8	—	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	25	—	ns	$V_{DD} = -15V, V_{GS} = -4.5V$ ③
t_r	Rise Time	—	47	—		$I_D = -1.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	65	—		$R_G = 1.8\Omega$
t_f	Fall Time	—	70	—		See Figs. 19a & 19b
C_{iss}	Input Capacitance	—	5250	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	1300	—		$V_{DS} = -15V$
C_{rss}	Reverse Transfer Capacitance	—	880	—		$f = 1.0MHz$

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	170	mJ
I_{AR}	Avalanche Current ①	—	-17	A

Diode Characteristics

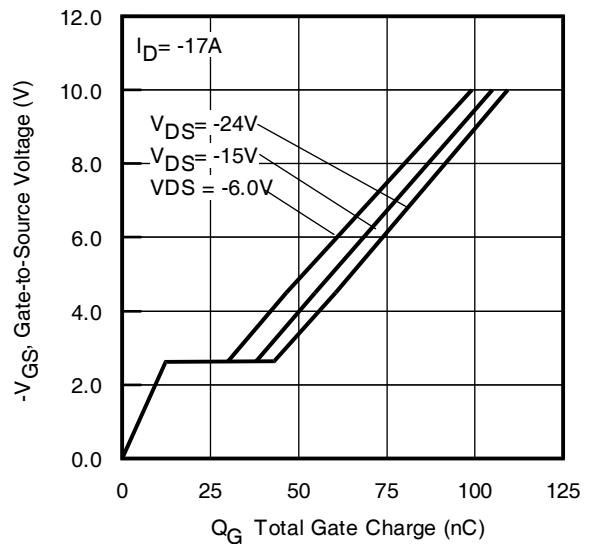
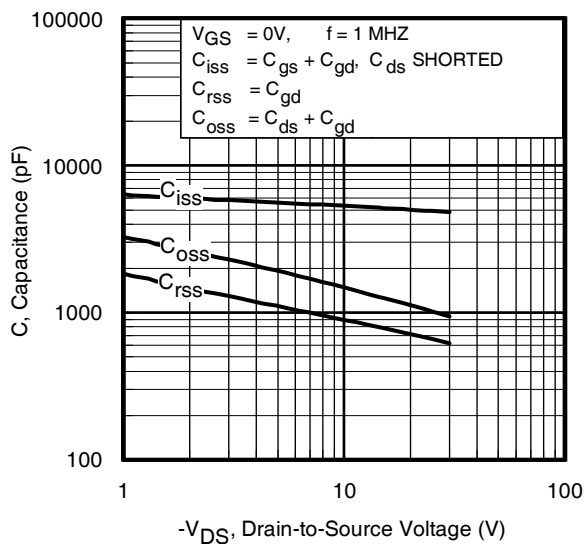
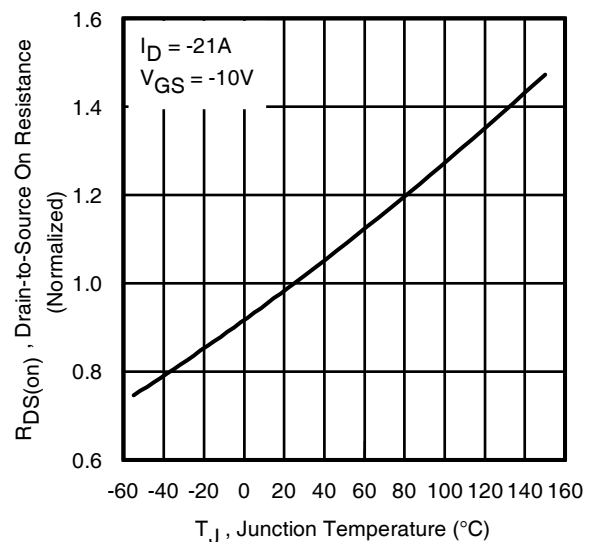
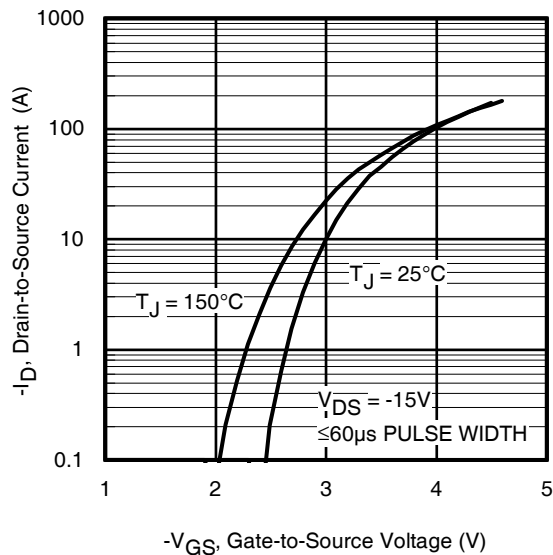
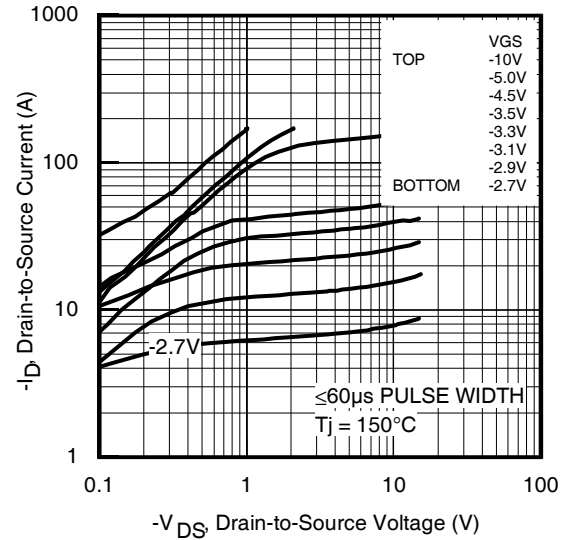
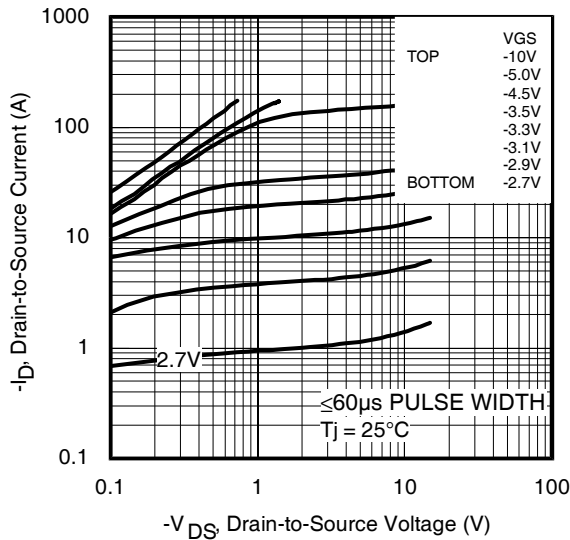
	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-3.1	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-170		
V_{SD}	Diode Forward Voltage	—	—	-1.2	V	$T_J = 25^\circ\text{C}, I_S = -3.1A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	42	63	ns	$T_J = 25^\circ\text{C}, I_F = -3.1A, V_{DD} = -24V$
Q_{rr}	Reverse Recovery Charge	—	42	63	nC	$di/dt = 100/\mu s$ ③

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑤	—	1.6	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction-to-Ambient ④	—	40	
$R_{\theta JA}$	Junction-to-Ambient ($t < 10s$) ④	—	35	

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 1.1mH$, $R_G = 50\Omega$, $I_{AS} = -17A$.
- ③ Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board.
- ⑤ R_θ is measured at T_J of approximately 90°C .
- ⑥ For DESIGN AID ONLY, not subject to production testing.



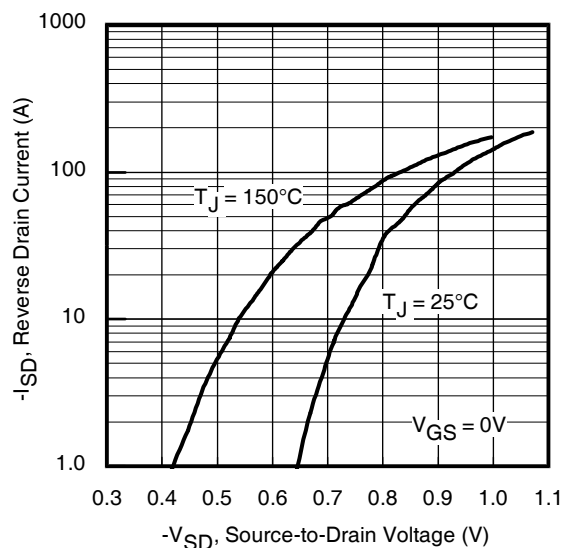


Fig 7. Typical Source-Drain Diode Forward Voltage

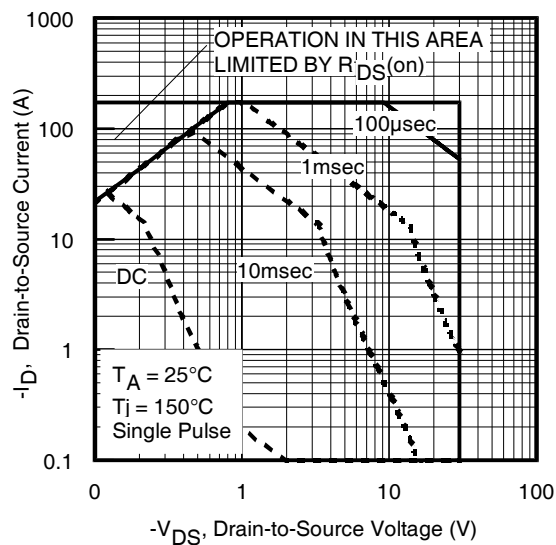


Fig 8. Maximum Safe Operating Area

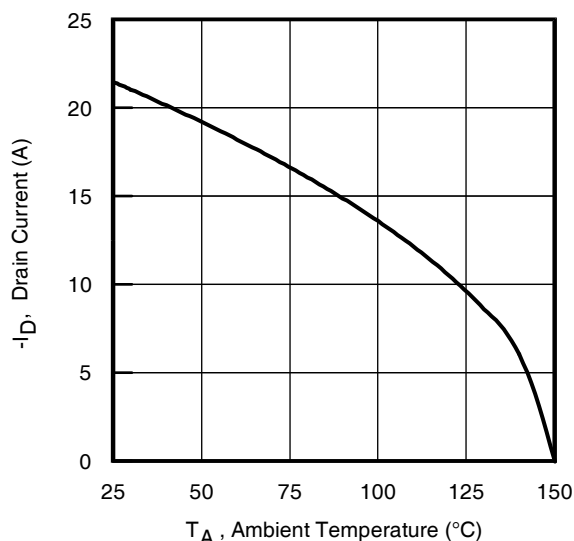


Fig 9. Maximum Drain Current vs. Ambient Temperature

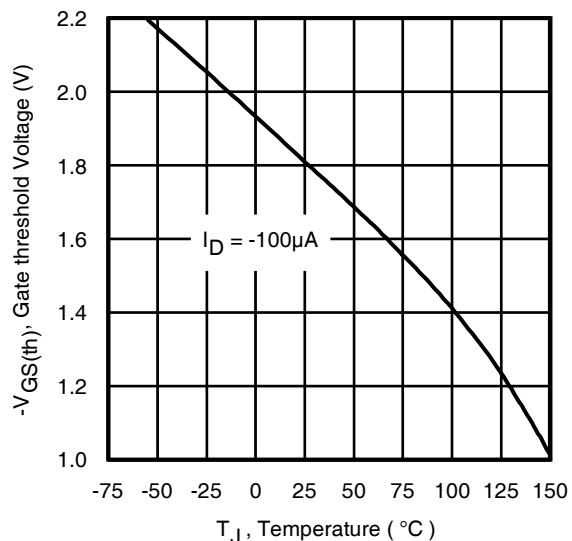


Fig 10. Threshold Voltage vs. Temperature

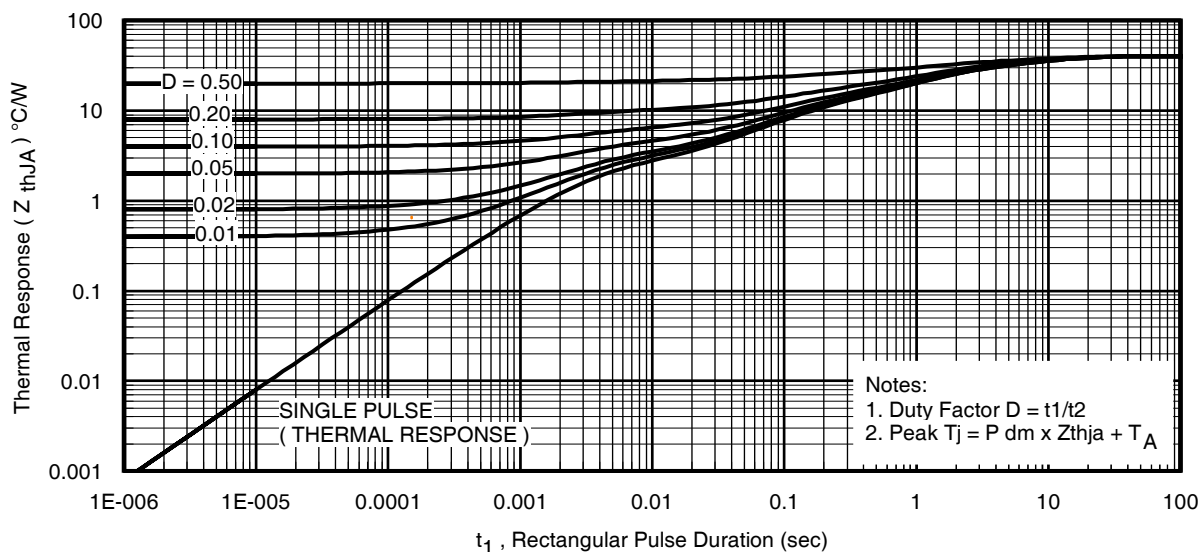


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

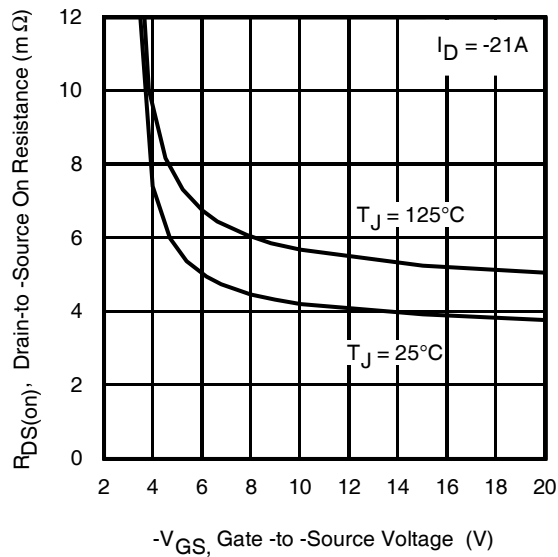


Fig 12. On-Resistance vs. Gate Voltage

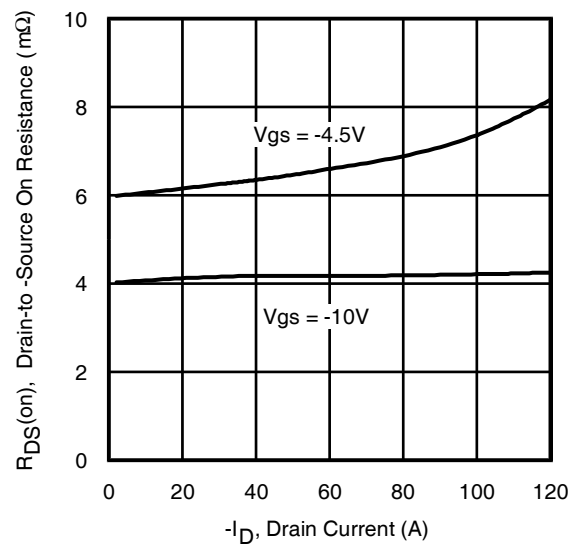


Fig 13. Typical On-Resistance vs. Drain Current

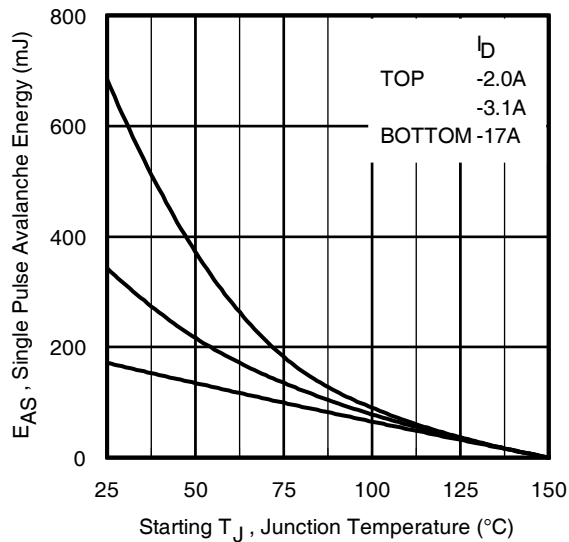


Fig 14. Maximum Avalanche Energy vs. Drain Current

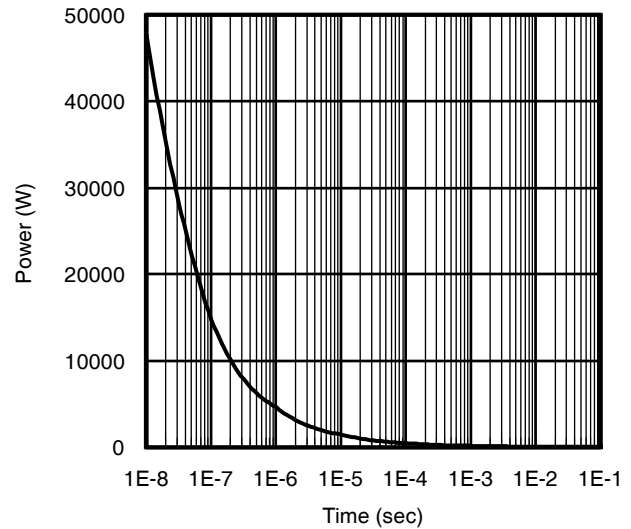


Fig 15. Typical Power vs. Time

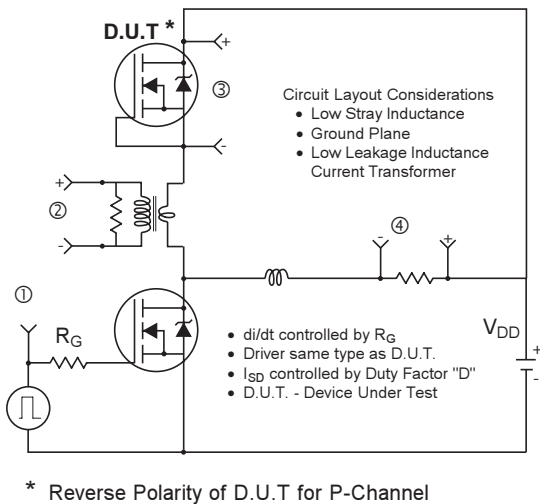
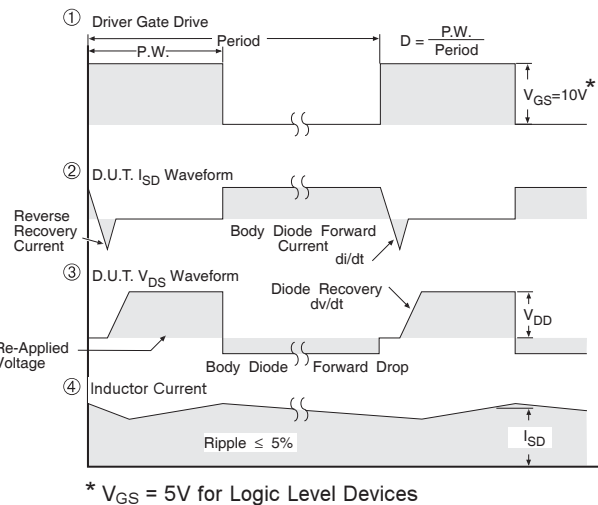


Fig 16. Diode Reverse Recovery Test Circuit for P-Channel HEXFET® Power MOSFETs



* $V_{GS} = 5V$ for Logic Level Devices

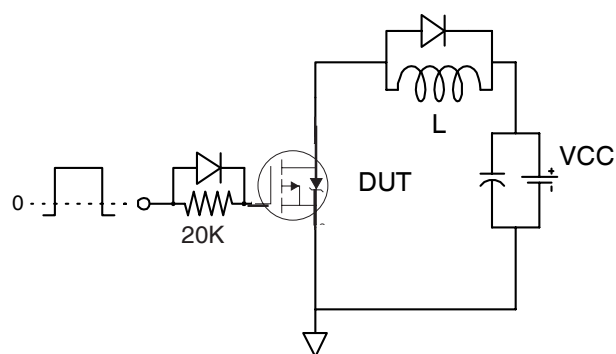


Fig 17a. Gate Charge Test Circuit

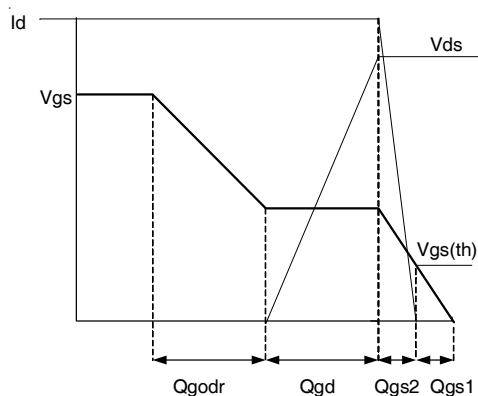


Fig 17b. Gate Charge Waveform

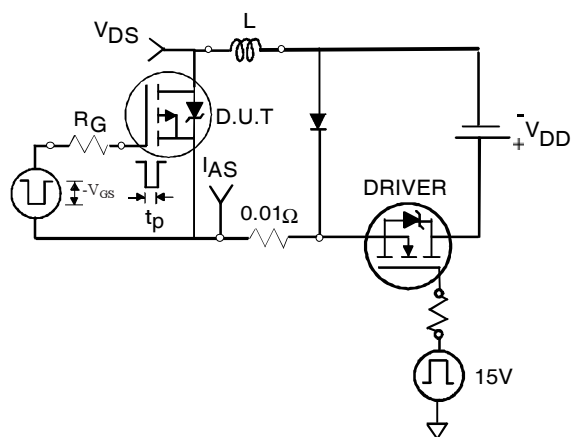


Fig 18a. Unclamped Inductive Test Circuit

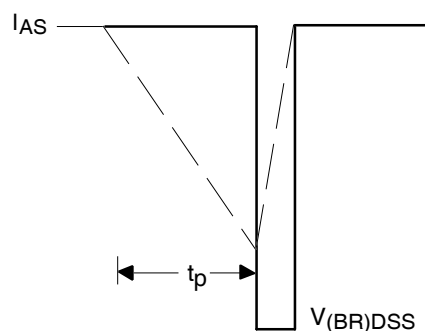


Fig 18b. Unclamped Inductive Waveforms

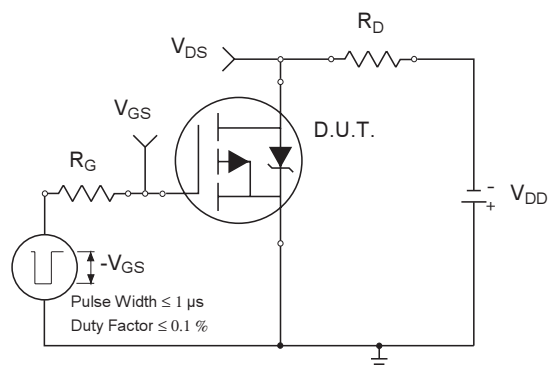


Fig 19a. Switching Time Test Circuit

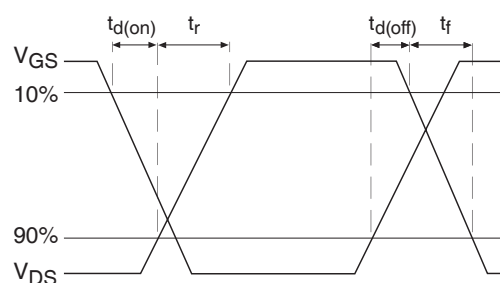
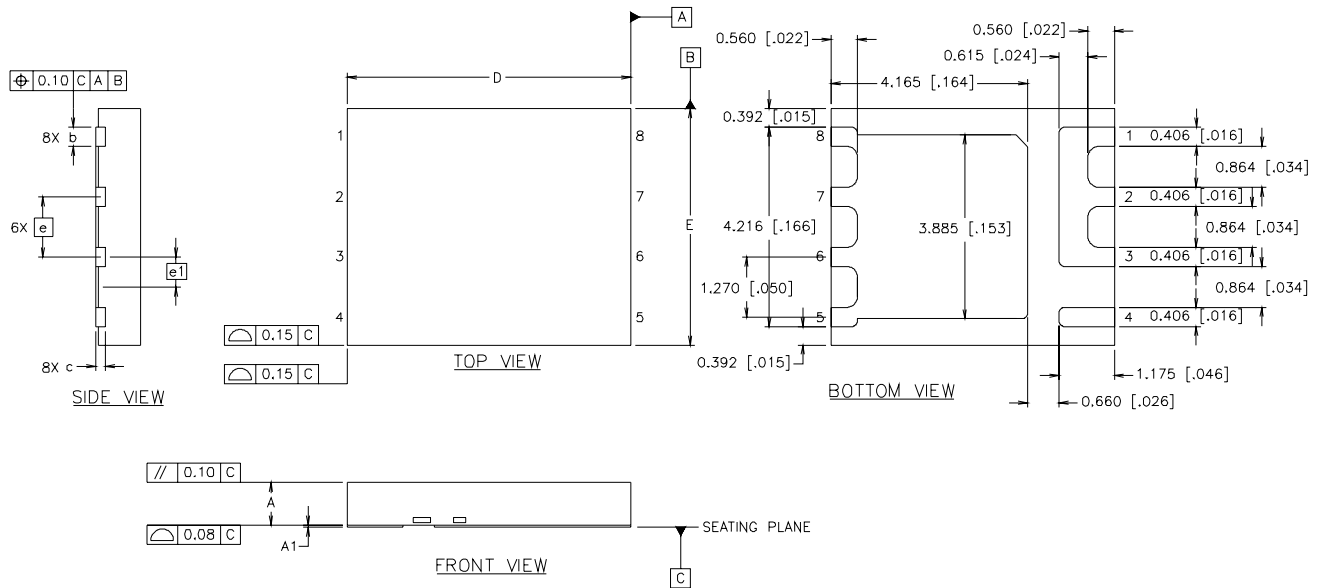


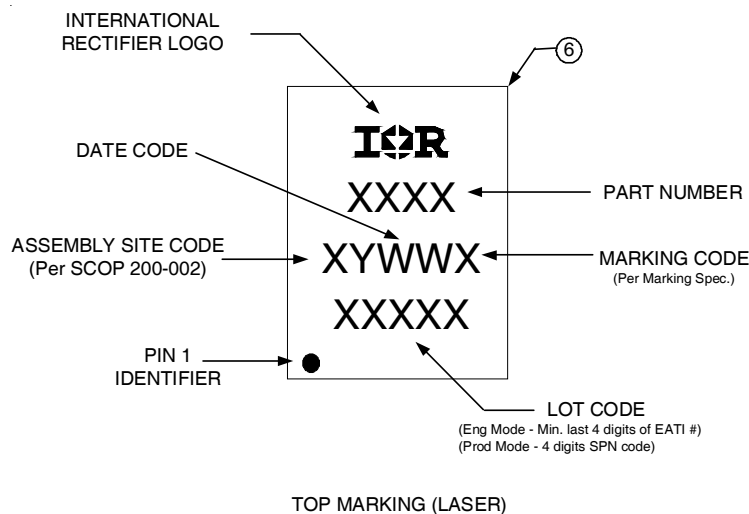
Fig 19b. Switching Time Waveforms

PQFN Package Details



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0315	.0394	0.800	1.000
A1	.0000	.0020	0.000	0.050
b	.0140	.0180	0.356	0.456
c	.0080 REF.		0.203 REF.	
D	.2362 BASIC		6.0 BASIC	
E	.1969 BASIC		5.0 BASIC	
e	.0500 BASIC		1.270 BASIC	
e1	.0250 BASIC		0.635 BASIC	

PQFN Part Marking

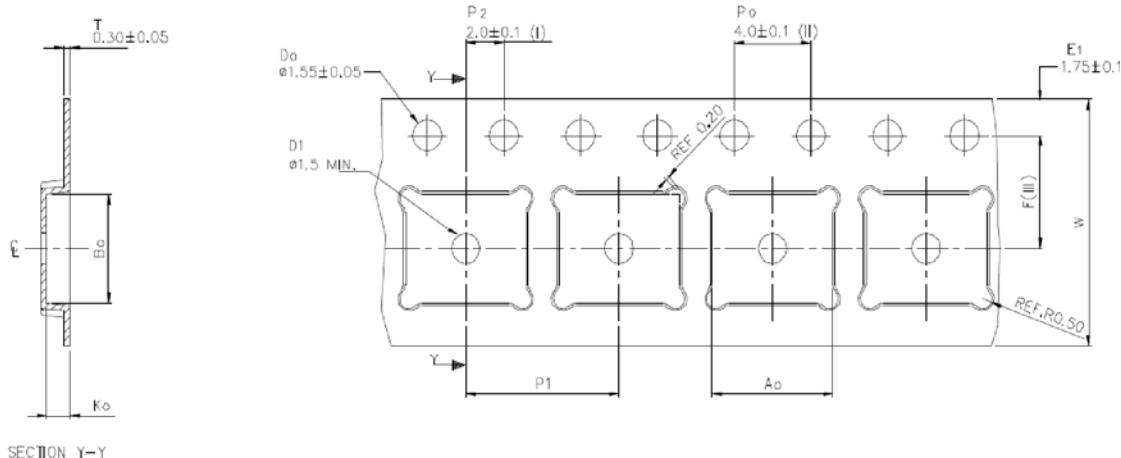


Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

IRFH9310PbF

PQFN Tape and Reel

International
IR Rectifier



A_0	6.30 ± 0.1
B_0	5.30 ± 0.1
K_0	1.20 ± 0.1
F	5.50 ± 0.1
P_1	8.00 ± 0.1
W	12.00 ± 0.3

- (I) Measured from centreline of sprocket hole to centreline of pocket.
- (II) Cumulative tolerance of 10 sprocket holes is ± 0.20 .
- (III) Measured from centreline of sprocket hole to centreline of pocket.
- (IV) Other material available.
- (V) Typical SR of form tape Max 10^{-9} OHM/SQ

ALL DIMENSIONS IN MILLIMETRES UNLESS OTHERWISE STATED.

Qualification Information[†]

Qualification level	Consumer ^{††}	
	(per JEDEC JESD47F ^{†††} guidelines)	
Moisture Sensitivity Level	PQFN 5mm x 6mm	MSL2 (per JEDEC J-STD-020D ^{†††})
RoHS Compliant	Yes	

[†] Qualification standards can be found at International Rectifier's web site

<http://www.irf.com/product-info/reliability>

^{††} Higher qualification ratings may be available should the user have such requirements.

Please contact your International Rectifier sales representative for further information:

<http://www.irf.com/whoto-call/salesrep/>

^{†††} Applicable version of JEDEC standard at the time of product release.

^{††††} Higher MSL ratings may be available for the specific package types listed here. Please contact your International Rectifier sales representative for further information: <http://www.irf.com/whoto-call/salesrep/>

Data and specifications subject to change without notice.

International
IR Rectifier

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